



### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(ON)</sub> max       | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |
|----------------------|-------------------------------|--|
| -30V                 | 5Ω @ V <sub>GS</sub> = -4.5V  |  |
|                      | 6Ω @ V <sub>GS</sub> = -2.5V  | -0.2A  |
|                      | $7\Omega @ V_{GS} = -1.8V$    | -U.ZA  |
|                      | 10Ω @ V <sub>GS</sub> = -1.5V |  |

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch



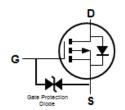


## Features and Benefits

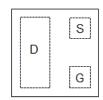
- Low Package Profile, 0.42mm Maximum Package height
- 0.62mm x 0.62mm Package Footprint
- Low On-Resistance
- Very low Gate Threshold Voltage, 1.0V max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)







Top View Package Pin Configuration

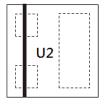
### Ordering Information (Note 4)

| Part Number   | Case         | Packaging       |
|---------------|--------------|-----------------|
| DMP32D9UFZ-7B | X2-DFN0606-3 | 10K/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Top View Bar Denotes Gate and Source Side

U2 = Product Type Marking Code



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |                 |                                  | Symbol          | Value        | Units |
|---|-----------------|----------------------------------|-----------------|--------------|-------|
| Drain-Source Voltage                                      |                 |                                  | $V_{DSS}$       | -30          | V     |
| Gate-Source Voltage                                       |                 |                                  | $V_{GSS}$       | ±10          | V     |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V | Steady<br>State | $T_A = +25$ °C<br>$T_A = +70$ °C | I <sub>D</sub>  | -200<br>-100 | mA    |
| Pulsed Drain Current (Note 6)                             |                 |                                  | I <sub>DM</sub> | -500         | mA    |

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic   | Symbol       | Value                            | Units       |      |
|--|--------------|----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                               | Steady State | P <sub>D</sub>                   | 390         | mW   |
| Thermal Resistance, Junction to Ambient (Note 5)  Steady State |              | $R_{	heta JA}$                   | 322         | °C/W |
| Operating and Storage Temperature Range                        |              | T <sub>J,</sub> T <sub>STG</sub> | -55 to +150 | °C   |

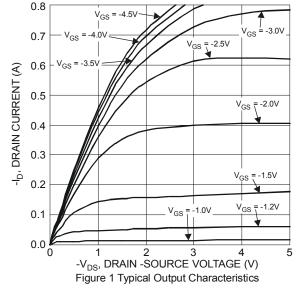
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

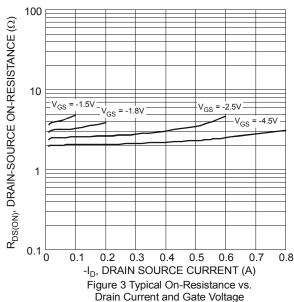
| Characteristic  |                      | Min  | Тур   | Max  | Unit | Test Condition  |
|---|----------------------|------|-------|------|------|---|
| OFF CHARACTERISTICS (Note 7)                            |                      |      |       |      |      |   |
| Drain-Source Breakdown Voltage                          |                      | -30  | _     | _    | V    | $V_{GS} = 0V, I_D = -250\mu A$                            |
| Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C | I <sub>DSS</sub>     |      | _     | 100  | nA   | V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V              |
| Gate-Source Leakage                                     |                      | _    | _     | ±10  | μA   | $V_{GS} = \pm 10V$ , $V_{DS} = 0V$                        |
| ON CHARACTERISTICS (Note 7)                             | _                    |      |       |      |      |   |
| Gate Threshold Voltage                                  | V <sub>GS(th)</sub>  | -0.4 | _     | -1.0 | V    | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                     |
|   |                      |      | _     | 5    |      | $V_{GS} = -4.5V$ , $I_D = -100$ mA                        |
|   |                      |      | _     | 6    |      | $V_{GS} = -2.5V$ , $I_D = -50mA$                          |
| Static Drain-Source On-Resistance                       | R <sub>DS (ON)</sub> | _    | _     | 7    | Ω    | $V_{GS} = -1.8V, I_D = -20mA$                             |
|   |                      | -    | _     | 10   |      | $V_{GS} = -1.5V, I_D = -10mA$                             |
|   |                      |      | 6     | _    |      | $V_{GS} = -1.2V, I_D = -1mA$                              |
| Diode Forward Voltage                                   |                      | _    | -0.75 | -1.0 | V    | $V_{GS} = 0V, I_{S} = -10mA$                              |
| DYNAMIC CHARACTERISTICS (Note 8)                        |                      |      |       |      |      |   |
| Input Capacitance                                       |                      |      | 22.5  | _    | pF   | 45)()(  |
| Output Capacitance                                      |                      |      | 2.9   | _    | pF   | $V_{DS} = -15V, V_{GS} = 0V,$<br>- f = 1.0MHz             |
| Reverse Transfer Capacitance                            | C <sub>rss</sub>     | _    | 2.1   | _    | pF   | 1 - 1.00012   |
| Total Gate Charge                                       |                      | _    | 0.35  | _    | nC   | 45)   |
| Gate-Source Charge                                      |                      | _    | 0.06  | _    | nC   | $V_{GS} = -4.5V$ , $V_{DS} = -15V$ ,<br>$I_{D} = -200$ mA |
| Gate-Drain Charge                                       | $Q_{gd}$             | _    | 0.09  | _    | nC   | - 1D = -200111A   |
| Turn-On Delay Time                                      | t <sub>D(on)</sub>   | _    | 3.1   | _    | ns   |   |
| Turn-On Rise Time                                       |                      | _    | 2.3   | _    | ns   | $V_{DD} = -10V, V_{GS} = -4.5V,$                          |
| Turn-Off Delay Time                                     |                      | _    | 19.9  | _    | ns   | $R_G = 6\Omega$ , $I_D = -200 \text{mA}$                  |
| Turn-Off Fall Time                                      |                      | -    | 10.5  |      | ns   |   |

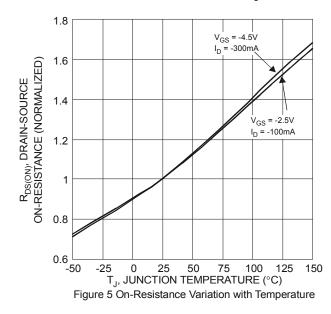
Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.

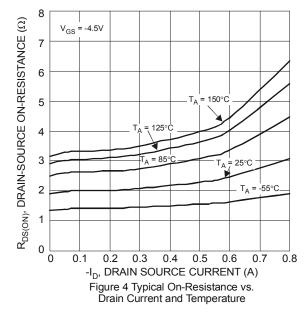








0.6  $V_{DS} = -5.0V$ 0.5 -I<sub>D</sub>, DRAIN CURRENT (A) 0.4 0.3 0.2 T<sub>A</sub> = 150°,Ċ T<sub>A</sub> = 85°C 0.1  $\mathsf{T}_\mathsf{A}$ . 125°€ = 25°C -55°C 0 0.5 1 1.5 2 2.5 -V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) 3 Figure 2 Typical Transfer Characteristics



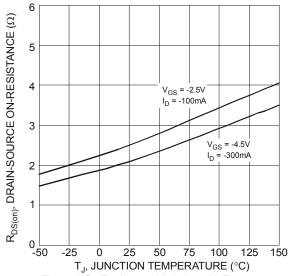


Figure 6 On-Resistance Variation with Temperature

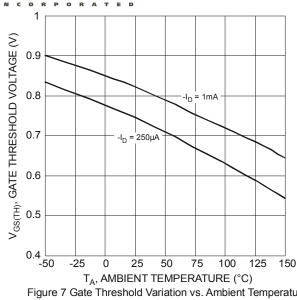
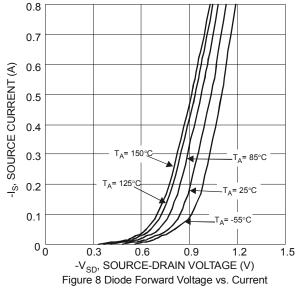
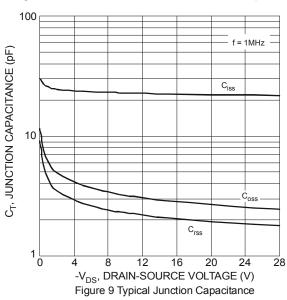
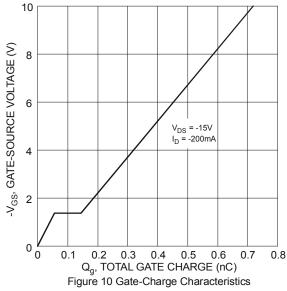
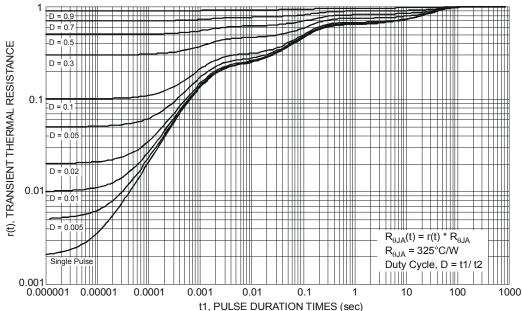


Figure 7 Gate Threshold Variation vs. Ambient Temperature





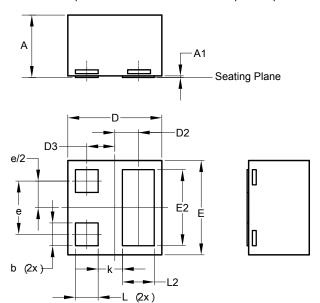






## **Package Outline Dimensions**

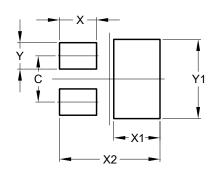
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| X2-DFN0606-3         |           |      |      |  |  |
|----------------------|-----------|------|------|--|--|
| Dim                  | Min       | Max  | Тур  |  |  |
| Α                    | 0.36      | 0.42 | 0.39 |  |  |
| A1                   | 0         | 0.05 | 0.02 |  |  |
| b                    | 0.10      | 0.20 | 0.15 |  |  |
| D                    | 0.57      | 0.67 | 0.62 |  |  |
| D2                   | 0.155 BSC |      |      |  |  |
| D3                   | 0.185 BSC |      |      |  |  |
| E                    | 0.57      | 0.67 | 0.62 |  |  |
| E2                   | 0.40      | 0.60 | 0.50 |  |  |
| е                    | 0.35 BSC  |      |      |  |  |
| k                    | 0.16 REF  |      |      |  |  |
| L                    | 0.09      | 0.21 | 0.15 |  |  |
| L2                   | 0.11      | 0.31 | 0.21 |  |  |
| All Dimensions in mm |           |      |      |  |  |

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value<br>(in mm) |  |  |
|------------|------------------|--|--|
| С          | 0.350            |  |  |
| Х          | 0.280            |  |  |
| X1         | 0.350            |  |  |
| X2         | 0.760            |  |  |
| Y          | 0.200            |  |  |
| Y1         | 0.600            |  |  |



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